

NSR30CM3

Dual Common Cathode Schottky Barrier Diodes

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand-held and portable applications where space is limited.

Features

- Extremely Fast Switching Speed
- Low Forward Voltage – 0.35 V (Typ) @ $I_F = 10$ mA
- This is a Pb-Free Device

MAXIMUM RATINGS ($T_J = 125^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	30	Volts
Forward Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_F	190 1.9	mW mW/ $^\circ\text{C}$
Forward Current (DC)	I_F	200 Max	mA
Junction Temperature	T_J	125 Max	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	525	$^\circ\text{C}/\text{W}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

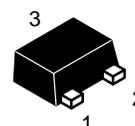
1. FR-4 board with minimum mounting pad.



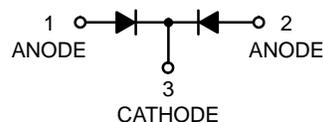
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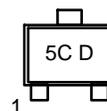
30 VOLTS DUAL COMMON CATHODE SCHOTTKY BARRIER DIODES



SOT-723
CASE 631AA
STYLE 3



MARKING DIAGRAM



5C = Specific Device Code
D = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
NSR30CM3T5G	SOT-723 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

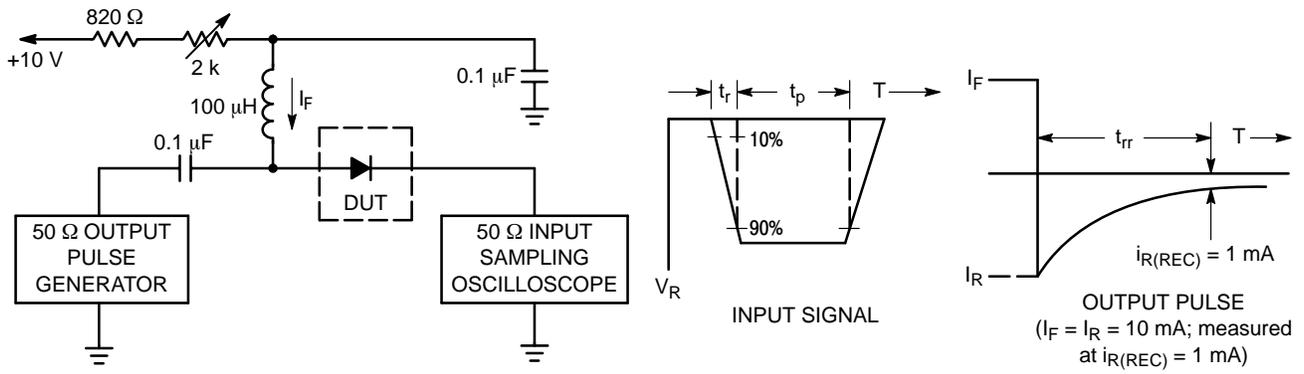
NSR30CM3

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage ($I_R = 10 \mu\text{A}$)	$V_{(BR)R}$	30	–	–	V
Total Capacitance ($V_R = 1.0 \text{ V}$, $f = 1.0 \text{ MHz}$)	C_T	–	7.6	10	pF
Reverse Leakage ($V_R = 25 \text{ V}$)	I_R	–	0.5	2.0	μA
Forward Voltage ($I_F = 0.1 \text{ mA}$) ($I_F = 1.0 \text{ mA}$) ($I_F = 10 \text{ mA}$) ($I_F = 30 \text{ mA}$) ($I_F = 100 \text{ mA}$)	V_F	– – – – –	0.22 0.29 0.35 0.41 0.52	0.24 0.32 0.40 0.50 0.80	V
Reverse Recovery Time ($I_F = I_R = 10 \text{ mA}$, $I_{R(\text{REC})} = 1.0 \text{ mA}$, Figure 1)	t_{rr}	–	–	5.0	ns
Forward Current (DC)	I_F	–	–	200	mA
Repetitive Peak Forward Current	I_{FRM}	–	–	300	mA
Non–Repetitive Peak Forward Current ($t < 1.0 \text{ s}$)	I_{FSM}	–	–	600	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
 2. Input pulse is adjusted so $I_{R(\text{peak})}$ is equal to 10 mA.
 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

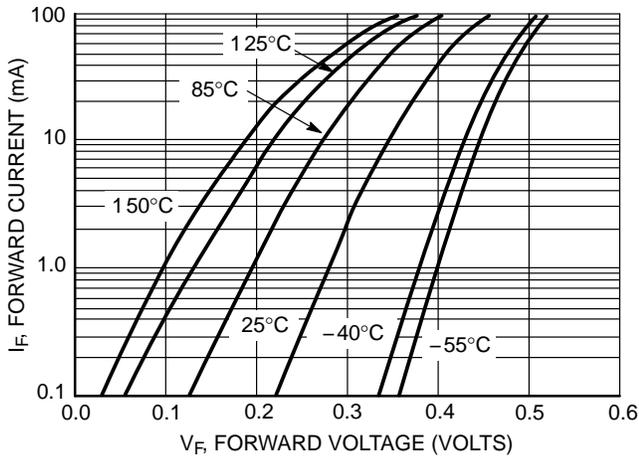


Figure 2. Forward Voltage

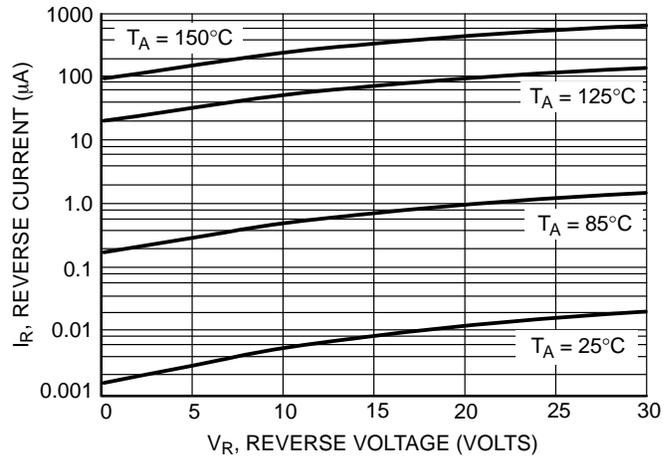


Figure 3. Leakage Current

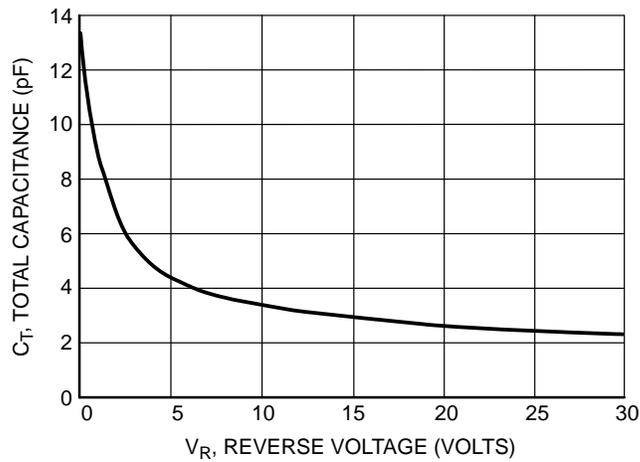
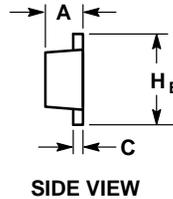
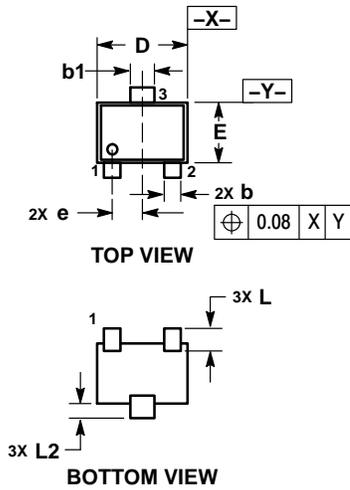


Figure 4. Total Capacitance

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PACKAGE DIMENSIONS

SOT-723
CASE 631AA
ISSUE D



NOTES:

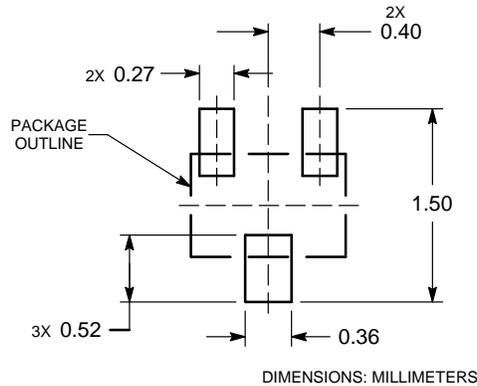
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
C	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H E	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25

STYLE 3:

1. ANODE
2. ANODE
3. CATHODE

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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